

5DS19B

Switching Diode

PHENITEC
SEMICONDUCTOR

Features

- High—speed

| Item | Characteristics |
|------------|-----------------|
| Wafer size | 5 inch |
| Chip size | 235*235um |

Maximum Ratings @25degC

| Item | Symbol | Value | Unit |
|--|--------|-----------|------|
| Repetitive Peak Reverse Voltage | VRRM | 100 | V |
| Continuous Reverse Voltage | VR | 100 | V |
| Continuous Forward Current | IF | 200 | mA |
| Repetitive Peak Forward Current | IFRM | 450 | mA |
| Non-Repetitive Peak Forward Current @t=1us | IFSM | 4 | A |
| Non-Repetitive Peak Forward Current @t=1ms | | 1 | A |
| Non-Repetitive Peak Forward Current @t=1s | | 0.5 | A |
| Total Power Dissipation | Ptot | 500 | mW |
| Storage Temperature | Tstg | -65to+200 | degC |
| Junction Temperature | Tj | 200 | degC |

Conformance Characteristic @25degC

| Symbol | Min | Max | Unit | Test Condition |
|--------|-----|------|------|------------------------------|
| VF1 | - | - | mV | IF=0.2mA |
| VF2 | 640 | 710 | mV | IF=5mA |
| VF3 | | 1010 | mV | IF=100mA |
| VF4 | | 1450 | mV | IF=500mA |
| IR1 | | 23 | nA | VR=20V |
| IR2 | | 45 | nA | VR=50V |
| IR3 | | 500 | nA | VR=75V |
| BV | 105 | | V | IR=10uA |
| CT | | 2 | pF | VR=0V,f=1MHz |
| trr | | 4 | nsec | IF=10mA, IR=10mA, irr=1mA |

Note Equivalent type : BAW62 SheetNo. Rev.